

**isc Silicon NPN Power Transistor**
**2SC4830**
**DESCRIPTION**

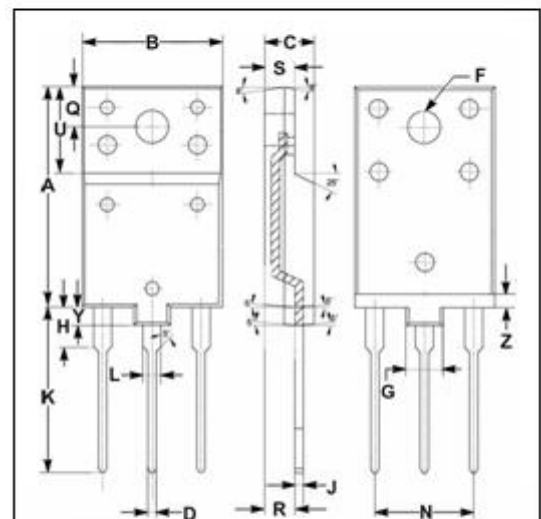
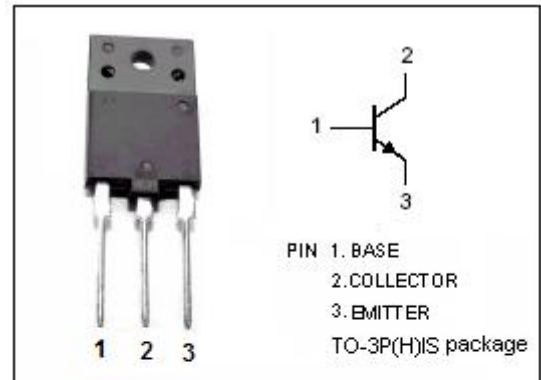
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V(\text{Min})$
- High Switching Speed
- Low Saturation Voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Horizontal deflection output for high resolution display.
- High speed switching power supply output applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Current-Peak	12	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	24.30	24.70
B	15.20	15.80
C	5.20	5.80
D	0.65	0.85
F	3.30	3.90
G	3.90	4.10
H	4.30	4.70
J	0.80	1.00
K	18.30	18.70
L	1.90	2.10
N	10.70	11.10
Q	4.40	4.60
R	3.30	3.70
S	3.20	3.40
U	9.50	9.70
Y	1.90	2.10
Z	1.40	1.60

## isc Silicon NPN Power Transistor

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## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 1A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	4		8	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		3		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		175		pF

Switching Times; Resistive Load

t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 4A; I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A; R <sub>L</sub> = 51 Ω			2.5	μ s
t <sub>f</sub>	Fall Time				0.2	μ s

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